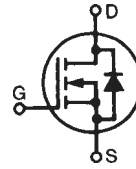


TrenchMV™ Power MOSFET

IXTA220N075T7

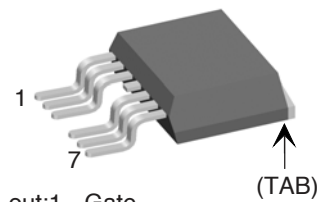
$V_{DSS} = 75 \text{ V}$
 $I_{D25} = 220 \text{ A}$
 $R_{DS(on)} \leq 4.5 \text{ m}\Omega$

N-Channel Enhancement Mode
Avalanche Rated



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 175°C	75	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 175°C ; $R_{GS} = 1 \text{ M}\Omega$	75	V
V_{GSM}	Transient	± 20	V
I_{D25}	$T_C = 25^\circ\text{C}$	220	A
I_{LRMS}	Package Current Limit, RMS	120	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	600	A
I_{AR}	$T_C = 25^\circ\text{C}$	25	A
E_{AS}	$T_C = 25^\circ\text{C}$	1.0	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$ $T_J \leq 175^\circ\text{C}$, $R_G = 3.3 \Omega$	3	V/ns
P_D	$T_C = 25^\circ\text{C}$	480	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
T_{solid}	Plastic body for 10 seconds	260	$^\circ\text{C}$
Weight		3	g

TO-263 (7-lead) (IXTA..7)



Pin-out: 1 - Gate
 2, 3 - Source
 4 - NC (cut)
 5, 6, 7 - Source
 TAB (8) - Drain

Features

- Ultra-low On Resistance
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- easy to drive and to protect
- 175 °C Operating Temperature

Advantages

- Easy to mount
- Space savings
- High power density

Applications

- Automotive
- Motor Drives
- 42V Power Bus
- ABS Systems
- DC/DC Converters and Off-line UPS
- Primary Switch for 24V and 48V Systems
- High Current Switching Applications

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	75		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	2.0		V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 150^\circ\text{C}$			5 μA 250 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 25 \text{ A}$, Note 1	3.6	4.5	$\text{m}\Omega$

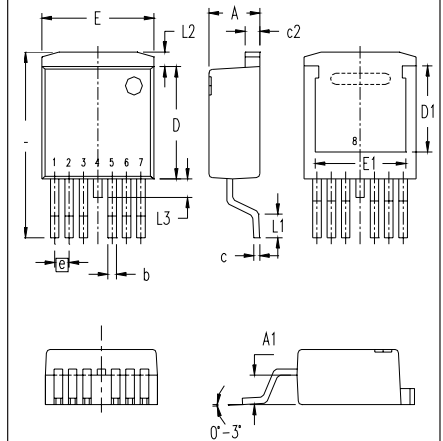
Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$(T_j = 25^\circ\text{C unless otherwise specified})$				
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 60\text{ A, Note 1}$	75	120	S
C_{iss}			7700	pF
C_{oss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		1100	pF
C_{rss}			230	pF
$t_{d(on)}$	Resistive Switching Times		29	ns
t_r	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 25\text{ A}$		65	ns
$t_{d(off)}$	$R_G = 3.3\ \Omega$ (External)		55	ns
t_f			47	ns
$Q_{g(on)}$			165	nC
Q_{gs}	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 25\text{ A}$		40	nC
Q_{gd}			50	nC
R_{thJC}				$0.31\ ^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$T_j = 25^\circ\text{C unless otherwise specified}$				
I_s	$V_{GS} = 0\text{ V}$			220 A
I_{SM}	Pulse width limited by T_{JM}			600 A
V_{SD}	$I_F = 25\text{ A}, V_{GS} = 0\text{ V, Note 1}$			1.0 V
t_{rr}	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 40\text{ V}, V_{GS} = 0\text{ V}$		80	ns

Notes: 1. Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$.

TO-263 (7-lead) (IXTA 7) Outline



- Pins: 1 - Gate
2, 3 - Source
4 - Drain
5, 6, 7 - Source
Tab (8) - Drain

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.085	.104	2.15	2.65
b	.026	.035	0.65	0.90
c	.016	.024	0.40	0.60
c2	.049	.055	1.25	1.40
D	.355	.370	9.00	9.40
D1	.272	.280	6.90	7.10
E	.386	.402	9.80	10.20
E1	.311	.319	7.90	8.10
e	.050 BSC		1.27 BSC	
L	.591	.614	15.00	15.60
L1	.091	.110	2.30	2.80
L2	.039	.059	1.00	1.50
L3	.000	.059	0.00	1.50

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537

Fig. 1. Output Characteristics @ 25°C

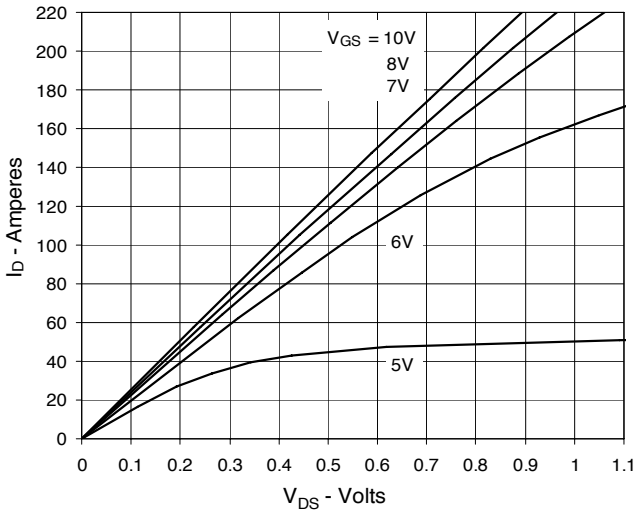


Fig. 2. Extended Output Characteristics @ 25°C

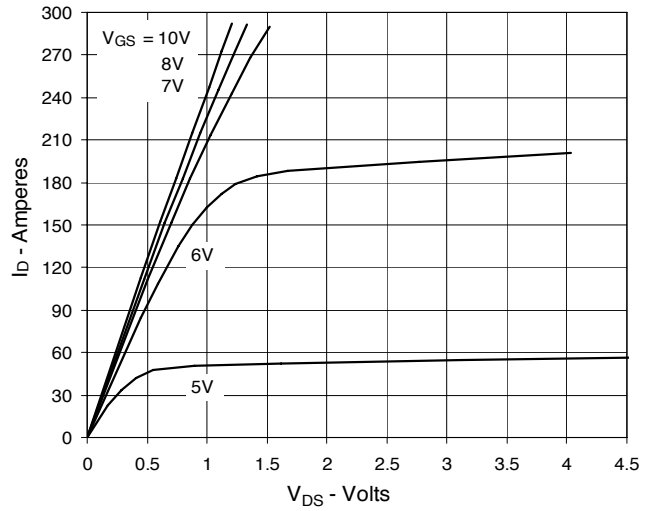


Fig. 3. Output Characteristics @ 150°C

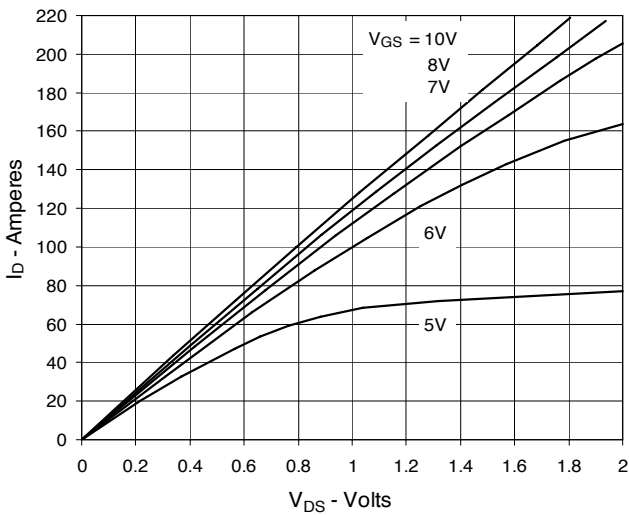


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 110A$ Value vs. Junction Temperature

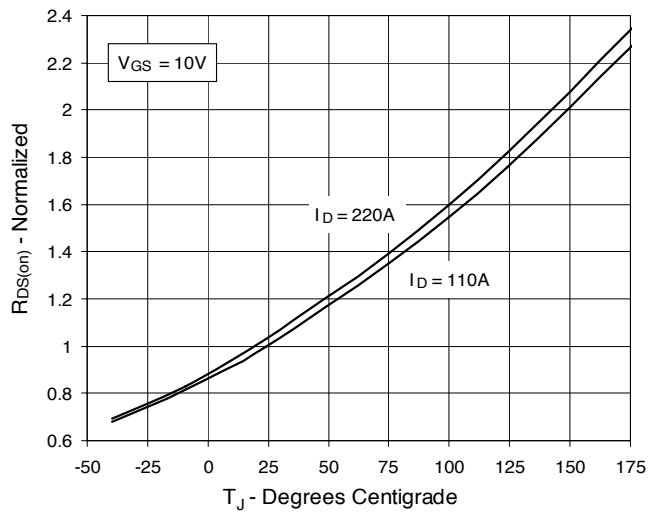


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 110A$ Value vs. Drain Current

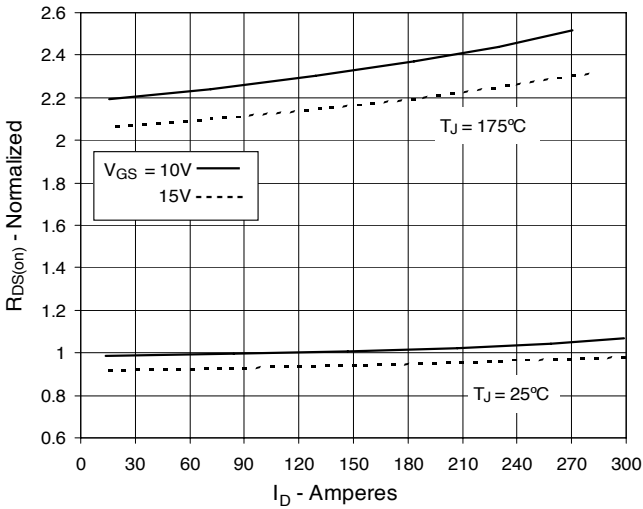


Fig. 6. Drain Current vs. Case Temperature

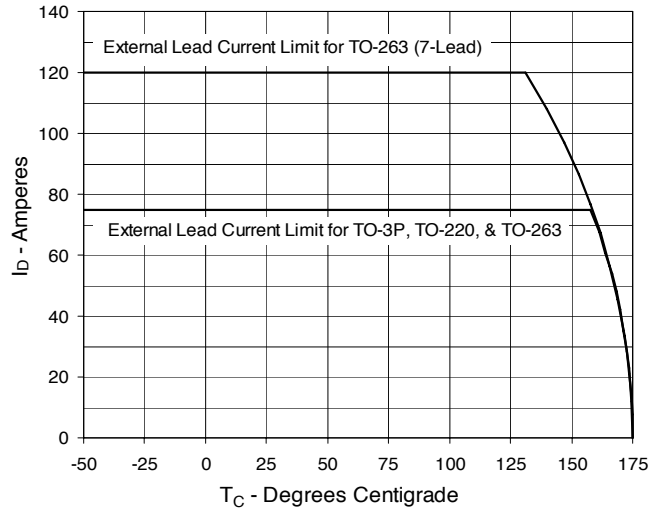


Fig. 7. Input Admittance

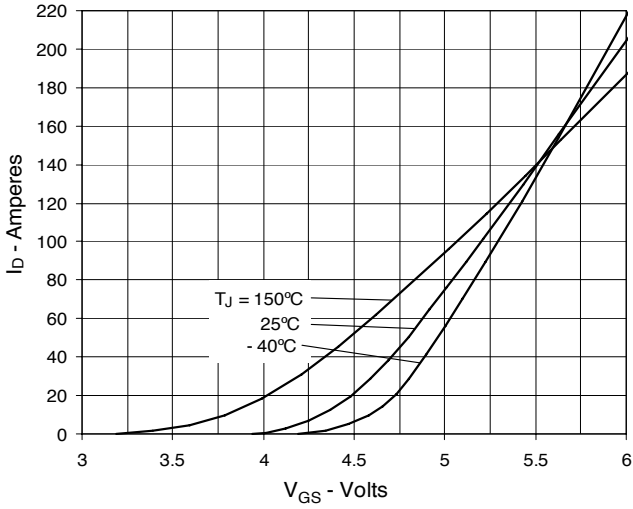


Fig. 8. Transconductance

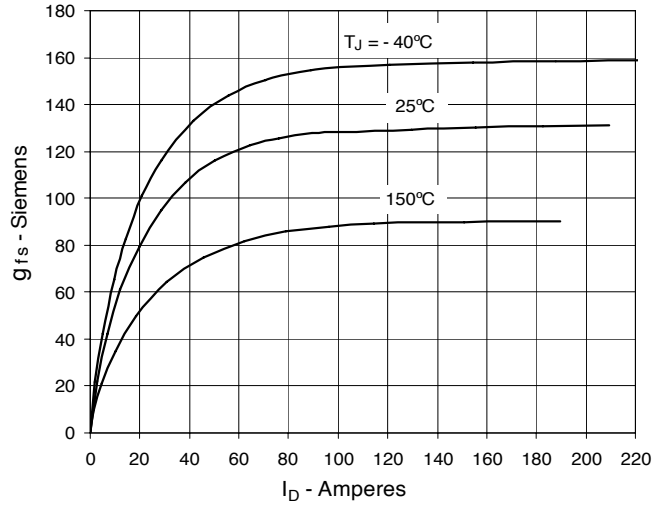


Fig. 9. Forward Voltage Drop of Intrinsic Diode

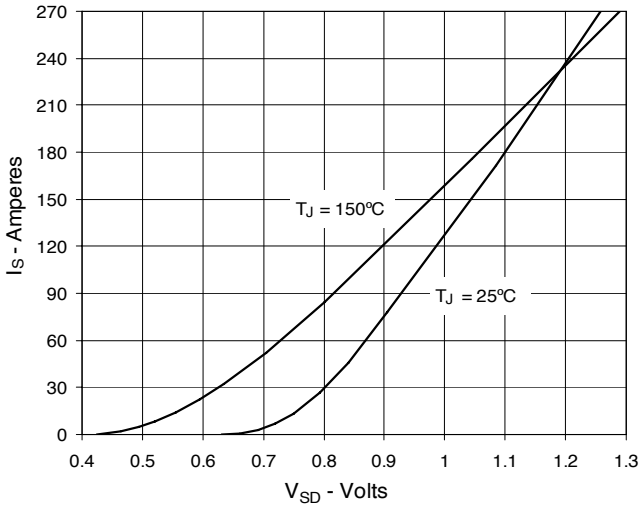


Fig. 10. Gate Charge

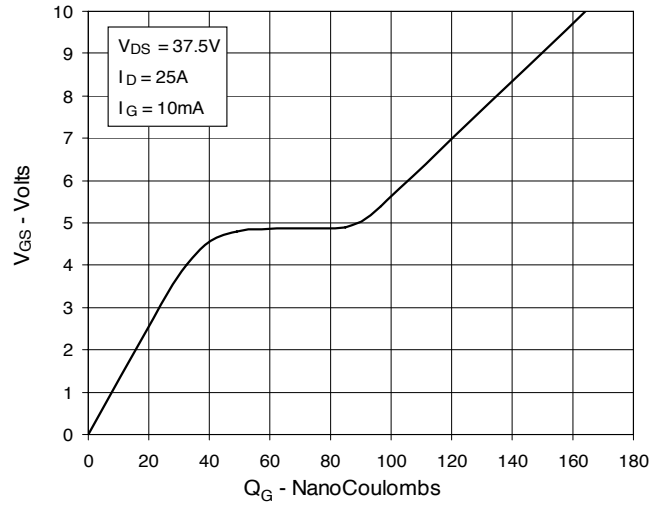


Fig. 11. Capacitance

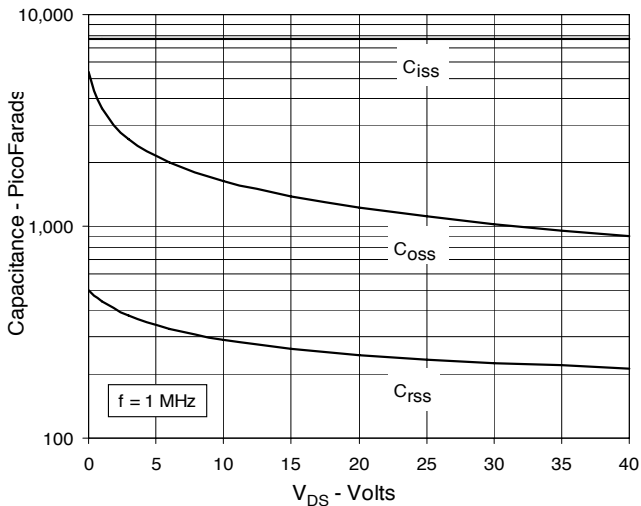


Fig. 12. Maximum Transient Thermal Impedance

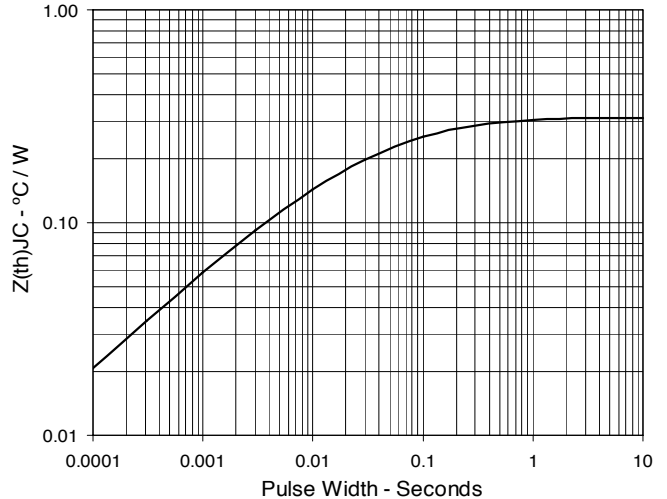


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

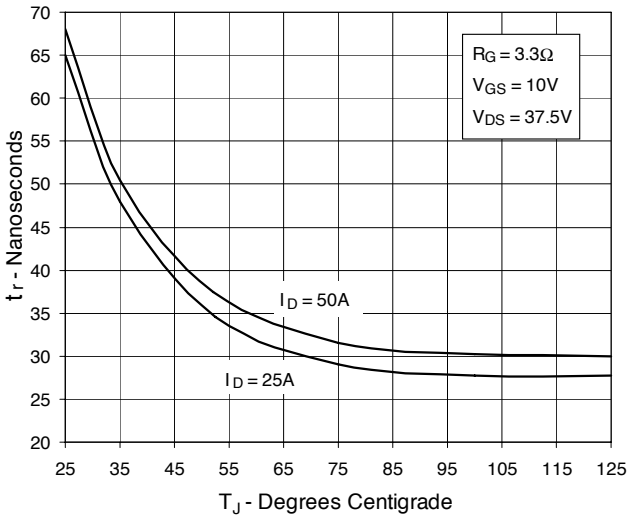


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

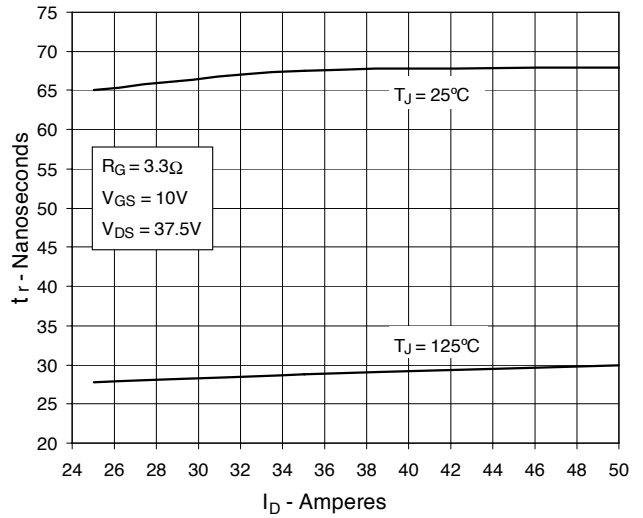


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

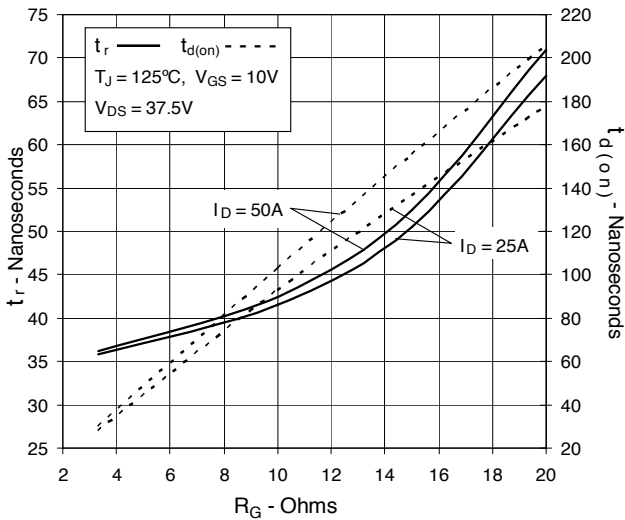


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

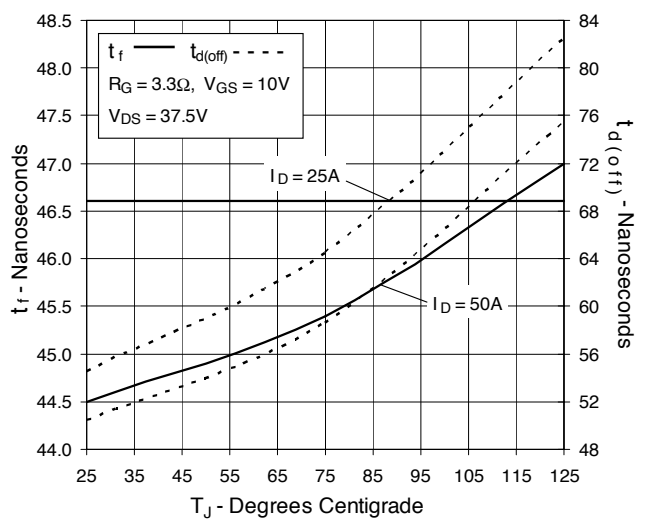


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

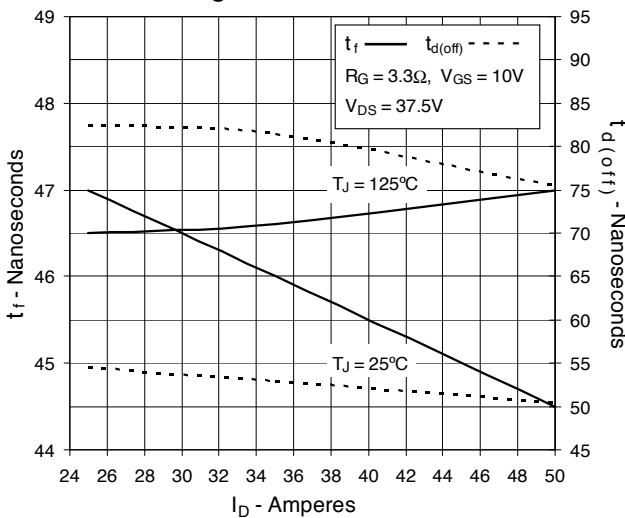


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

